

# BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu$ PC2745TB, $\mu$ PC2746TB

# 3 V, SUPER MINIMOLD SILICON MMIC WIDEBAND AMPLIFIER FOR MOBILE COMMUNICATIONS

#### **DESCRIPTION**

The  $\mu$ PC2745TB and  $\mu$ PC2746TB are silicon monolithic integrated circuits designed as buffer amplifier for mobile communications. These low current amplifiers operate on 3.0 V (1.8 V MIN.).

These ICs are manufactured using our 20 GHz ft NESATIII silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, these IC have excellent performance, uniformity and reliability.

#### **FEATURES**

Supply voltage : Recommended Vcc = 2.7 to 3.3 V

Circuit operation Vcc = 1.8 to 3.3 V

• Upper limit operating frequency :  $\mu$ PC2745TB; fu = 2.7 GHz TYP.@3 dB bandwidth

 $\mu$ PC2746TB; fu = 1.5 GHz TYP.@3 dB bandwidth

• High isolation :  $\mu$ PC2745TB; ISL = 38 dB TYP.@f = 500 MHz

 $\mu$ PC2746TB; ISL = 45 dB TYP.@f = 500 MHz

• Power gain :  $\mu$ PC2745TB; GP = 12 dB TYP.@f = 500 MHz

 $\mu$ PC2746TB; G<sub>P</sub> = 19 dB TYP.@f = 500 MHz

• Saturated output power :  $\mu$ PC2745TB; Po(sat) = -1 dBm TYP.@f = 500 MHz

 $\mu$ PC2746TB; Po(sat) = 0 dBm TYP.@f = 500 MHz

High-density surface mounting : 6-pin super minimold package (2.0 x 1.25 x 0.9 mm)

#### **APPLICATIONS**

1.5 GHz to 2.5 GHz communication system : μPC2745TB

800 MHz to 900 MHz communication system : μPC2746TB

#### ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPC2745TB-E3-A	6-pin super minimold	C1Q	Embossed tape 8 mm wide
μPC2746TB-E3-A		C1R	<ul><li>1, 2, 3 pins face the perforation side of the tape</li><li>Qty 3 kpcs/reel</li></ul>

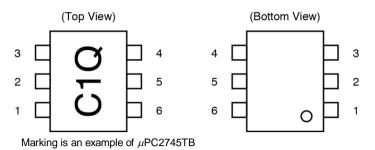
**Remark** To order evaluation samples, contact your nearby sales office. Part number for sample order: μPC2745TB-A, μPC2746TB-A

Fait number for sample order.  $\mu$ PG27451B-A,  $\mu$ PG27461B-A

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

# PIN CONNECTION



Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	Vcc

PRODUCT LINE-UP (TA =  $+25^{\circ}$ C, Vcc = 3.0 V, Zs = ZL = 50  $\Omega$ )

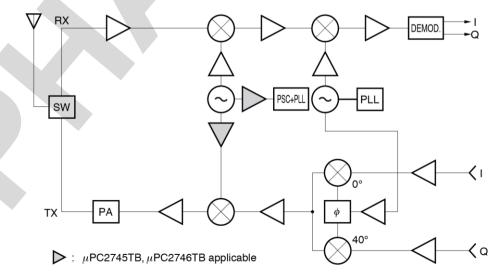
Part No.	fu (GHz)	Po(sat) (dBm)	G <sub>P</sub> (dB)	NF (dB)	Icc (mA)	Package	Making
μPC2745T	2.7	-1.0	12	6.0	7.5	6-pin minimold	C1Q
μPC2745TB						6-pin super minimold	
μPC2746T	1.5	0	19	4.0	7.5	6-pin minimold	C1R
μPC2746TB						6-pin super minimold	
μPC2747T	1.8	-7.0	12	3.3	5.0	6-pin minimold	C1S
μPC2747TB						6-pin super minimold	
μPC2748T	0.2 to 1.5	-3.5	19	2.8	6.0	6-pin minimold	C1T
μPC2748TB						6-pin super minimold	
μPC2749T	2.9	-6.0	16	4.0	6.0	6-pin minimold	C1U
μPC2749TB						6-pin super minimold	

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

Caution The package size distinguish between minimold and super minimold.

# SYSTEM APPLICATION EXAMPLE

# DIGITAL CELLULAR SYSTEM BLOCK DIAGRAM



# PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)	Function and Applications	Internal Equivalent Circuit
1	INPUT		0.87	Signal input pin. A internal matching circuit, configured with resistors, enables $50~\Omega$ connection over a wide band. this pin must be coupled to signal source with capacitor for DC cut.	6
2 3 5	GND	0		Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance difference.	
4	OUTPUT	_	1.95 2.54	Signal output pin. A internal matching circuit, configured with resistors, enables $50~\Omega$ connection over a wide band. This pin must be coupled to next stage with capacitor for DC cut.	3 2 5
6	Vcc	2.7 to 3.3	_	Power supply pin. This pin should be externally equipped with bypass capacity to minimize ground impedance.	

**Note** Pin voltage is measured at Vcc = 3.0 V. Above:  $\mu$ PC2745TB, Below:  $\mu$ PC2746TB

#### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc	T <sub>A</sub> = +25°C	4.0	V
Circuit Current	Icc	T <sub>A</sub> = +25°C	16	mA
Power Dissipation	Po	T <sub>A</sub> = +85°C <b>Note</b>	270	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		-55 to +150	°C
Input Power	Pin	T <sub>A</sub> = +25°C	0	dBm

**Note** Mounted on double-sided copper-clad  $50 \times 50 \times 1.6$  mm epoxy glass PWB

# RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc	2.7	3.0	3.3	V

# **ELECTRICAL CHARACTERISTICS**

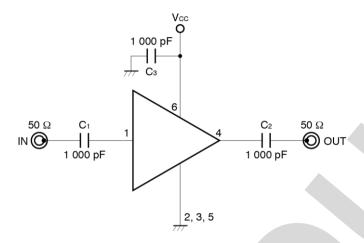
(TA = +25°C, Vcc = 3.0 V, Zs = ZL = 50  $\Omega$ , unless otherwise specified)

Description	0	Test Conditions	μ	μPC2745TB			μPC2746TB		
Parameter	Symbol		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	No signal	5.0	7.5	10.0	5.0	7.5	10.0	mA
Power Gain	GP	f = 500 MHz	9	12	14	16	19	21	dB
Noise Figure	NF	f = 500 MHz	_	6.0	7.5	_	4.0	5.5	dB
Upper Limit Operating Frequency	fu	3 dB down below from gain at f = 0.1 GHz	2.3	2.7	_	1.1	1.5	_	GHz
Isolation	ISL	f = 500 MHz	33	38		40	45	_	dB
Input Return Loss	RLin	f = 500 MHz	8	11	_	10	13	_	dB
Output Return Loss	RLout	f = 500 MHz	2.5	5.5	_	5.5	8.5	_	dB
Saturated Output Power	Po(sat)	$f = 500 \text{ MHz},$ $P_{in} = -6 \text{ dBm}$	-4.0	-1.0	_	-3.0	0	_	dBm

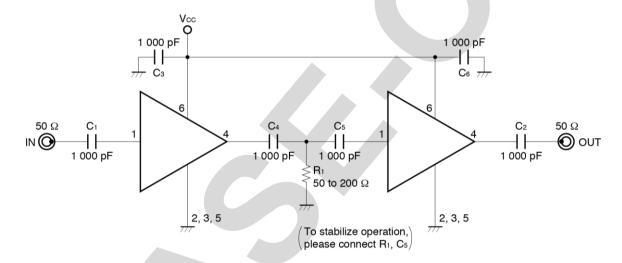
# STANDARD CHARACTERISTICS FOR REFERENCE (TA = +25°C, Vcc = 3.0 V, Zs = ZL = 50 $\Omega$ )

Parameter	Symbol	Test Conditions	Referen	ce Value	Unit
			μPC2745TB	μPC2746TB	
Circuit Current	Icc	Vcc = 1.8 V, No signal	4.5	4.5	mA
Power Gain	G₽	Vcc = 3.0 V, f = 1.0 GHz Vcc = 3.0 V, f = 2.0 GHz Vcc = 1.8 V, f = 0.5 GHz	12.0 11.0 7.0	18.5 — 14.0	dB
Noise Figure	NF	Vcc = 3.0 V, f = 1.0 GHz Vcc = 3.0 V, f = 2.0 GHz Vcc = 1.8 V, f = 0.5 GHz	5.5 5.7 8.0	4.2 — 5.0	dB
Upper Limit Operating Frequency	fu	Vcc = 1.8 V, 3 dB down below from gain at f = 0.1 GHz	1.8	1.1	GHz
Isolation	ISL	Vcc = 3.0 V, f = 1.0 GHz Vcc = 3.0 V, f = 2.0 GHz Vcc = 1.8 V, f = 0.5 GHz	33 30 35	38 — 37	dB
Input Return Loss	RLin	Vcc = 3.0 V, f = 1.0 GHz Vcc = 3.0 V, f = 2.0 GHz Vcc = 1.8 V, f = 0.5 GHz	13.0 14.0 6.5	10.0 — 10.0	dB
Output Return Loss	RLout	Vcc = 3.0 V, f = 1.0 GHz Vcc = 3.0 V, f = 2.0 GHz Vcc = 1.8 V, f = 0.5 GHz	6.5 8.5 6.0	8.5 — 9.5	dB
Saturated Output Power	Po(sat)	$Vcc = 3.0 \text{ V, } f = 1.0 \text{ GHz, } P_{in} = -6 \text{ dBm}$ $Vcc = 3.0 \text{ V, } f = 2.0 \text{ GHz, } P_{in} = -6 \text{ dBm}$ $Vcc = 1.8 \text{ V, } f = 0.5 \text{ GHz, } P_{in} = -10 \text{ dBm}$	-2.5 -3.5 -11.0	-1.0  -8.0	dBm
3rd Order Intermodulation Distortion	IМз	$\label{eq:Vcc} \begin{array}{l} \mbox{Vcc} = 3.0 \mbox{ V, } \mbox{Pout} = -10 \mbox{ dBm, } \mbox{f}_1 = 500 \mbox{ MHz, } \mbox{f}_2 = 502 \mbox{ MHz} \\ \mbox{Vcc} = 1.8 \mbox{ V, } \mbox{Pout} = -20 \mbox{ dBm, } \mbox{f}_1 = 500 \mbox{ MHz, } \mbox{f}_2 = 502 \mbox{ MHz} \\ \mbox{Vcc} = 3.0 \mbox{ V, } \mbox{Pout} = -10 \mbox{ dBm, } \mbox{f}_1 = 1 \mbox{ 000 \mbox{ MHz, }} \mbox{f}_2 = 1 \mbox{ 002 \mbox{ MHz}} \end{array}$	-30.0 -31.0 -26.0	-26.0 -37.0 	dBc

#### **TEST CIRCUIT**



#### **EXAMPLE OF APPLICATION CIRCUIT**



The application circuits and their parameters are for references only and are not intended for use in actual design-ins.

# CAPACITORS FOR THE Vcc, INPUT, AND OUTPUT PINS

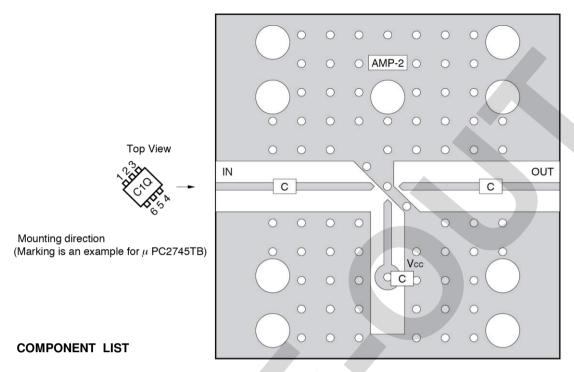
Capacitors of 1 000 pF are recommendable as the bypass capacitor for the Vcc pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the Vcc pin is used to minimize ground impedance of Vcc pin. So, stable bias can be supplied against Vcc fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitance are therefore selected as lower impedance against a 50  $\Omega$  load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

To obtain a flat gain from 100 MHz upwards, 1 000 pF capacitors are used in the test circuit. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 10 000 pF. Because the coupling capacitors are determined by equation, fc =  $1/(2\pi RC)$ .

#### ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



	Value
С	1 000 pF

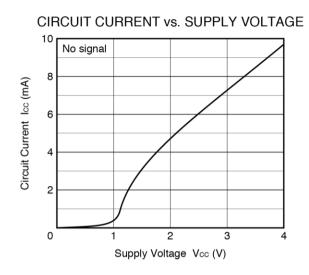
#### Notes

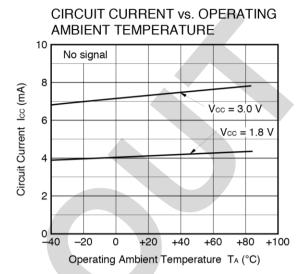
1.  $30 \times 30 \times 0.4$  mm double sided copper clad polyimide board.

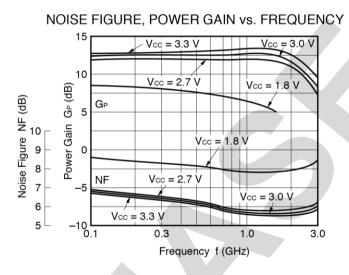
For more information on the use of this IC, refer to the following application note: USAGE AND APPLICATIONS OF 6-PIN MINI-MOLD, 6-PIN SUPER MINI-MOLD SILICON HIGH-FREQUENCY WIDEBAND AMPLIFIER MMIC (P11976E).

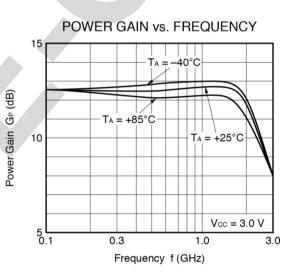
# TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

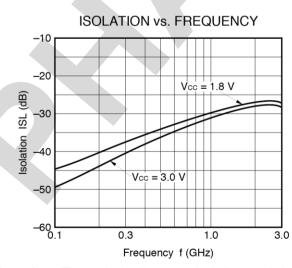
— μPC2745TB —

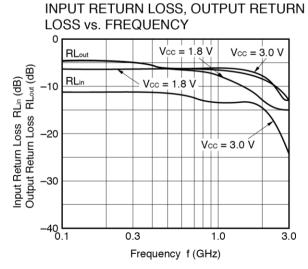






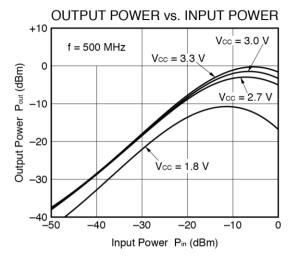


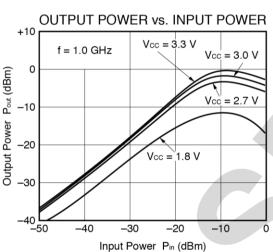


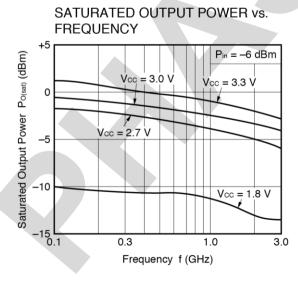


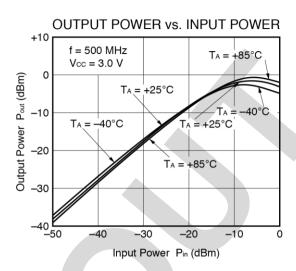
**Remark** The graphs indicate nominal characteristics.

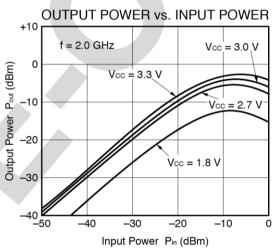
— μPC2745TB —

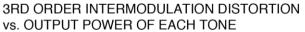


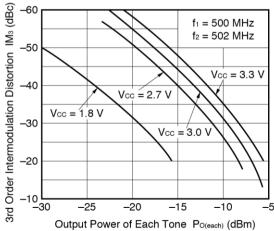










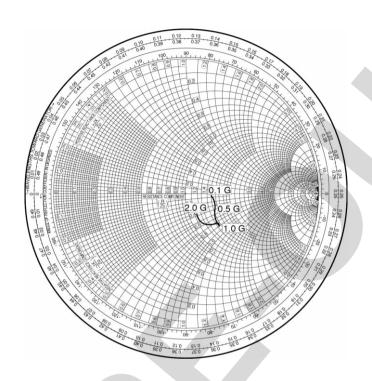


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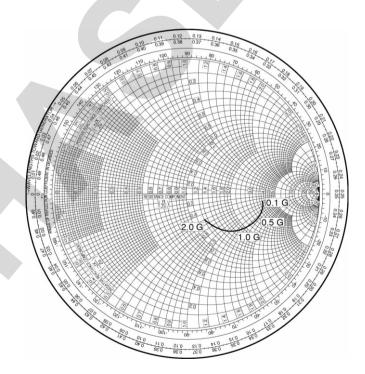
# SMITH CHART (Ta = +25°C, Vcc = 3.0 V)

— μPC2745TB —

S<sub>11</sub>-FREQUENCY

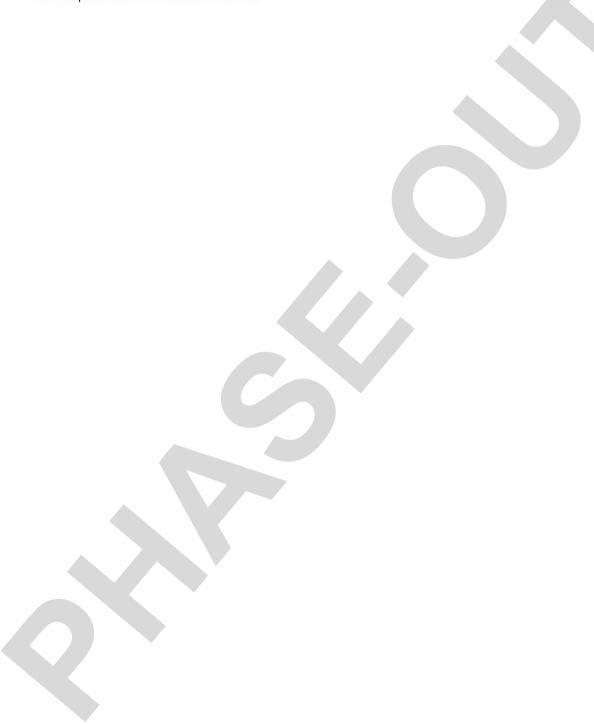


S<sub>22</sub>-FREQUENCY



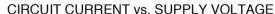
#### **S-PARAMETERS**

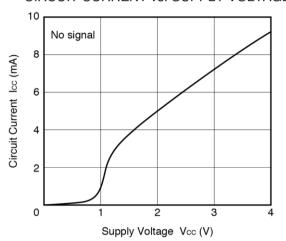
- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- · Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/



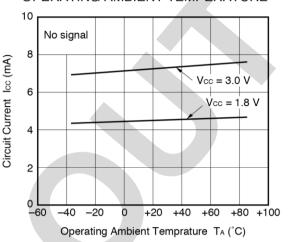
# TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

— μPC2746TB —

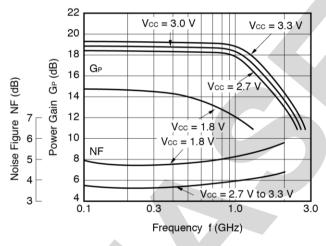




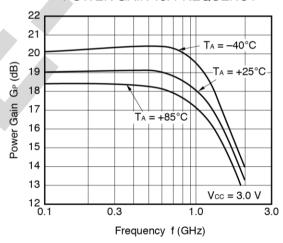
# CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE



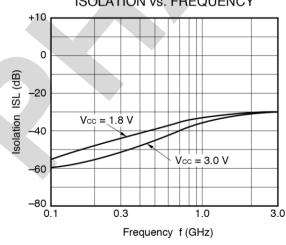
# NOISE FIGURE, POWER GAIN vs. FREQUENCY



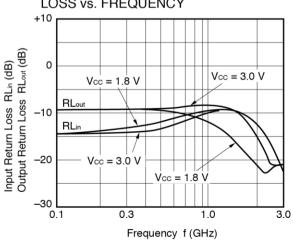
# POWER GAIN vs. FREQUENCY



ISOLATION vs. FREQUENCY

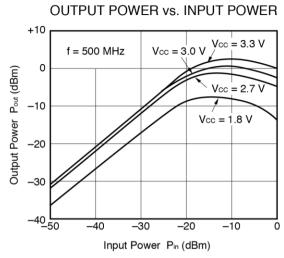


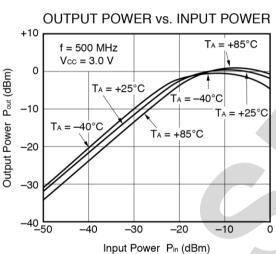
INPUT RETURN LOSS, OUTPUT RETURN LOSS vs. FREQUENCY

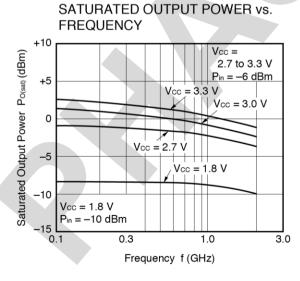


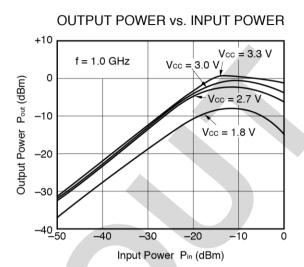
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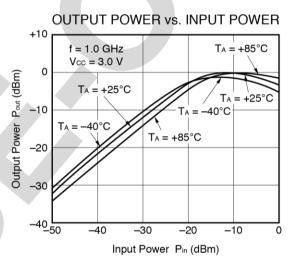
#### — μPC2746TB —

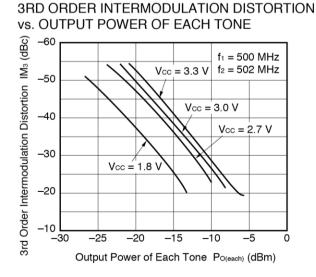










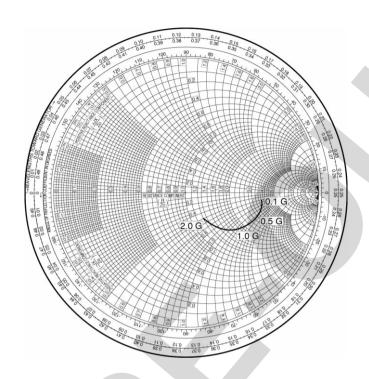


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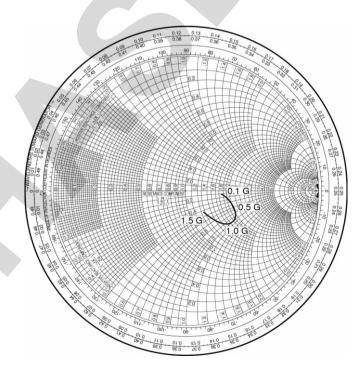
# SMITH CHART (Ta = +25°C, Vcc = 3.0 V)

— μPC2746TB —

S<sub>11</sub>-FREQUENCY

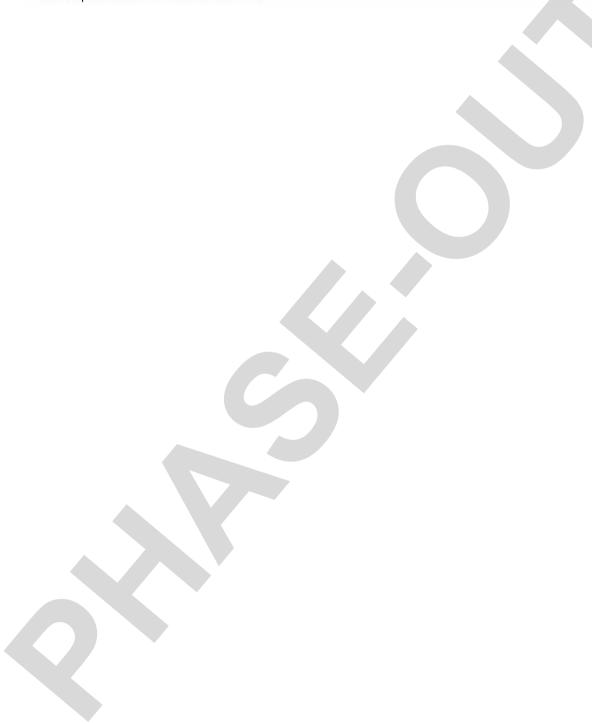


S<sub>22</sub>-FREQUENCY



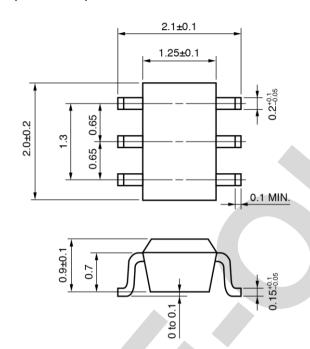
#### **S-PARAMETERS**

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- · Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL http://www.necel.com/microwave/en/



# PACKAGE DIMENSIONS

# 6-PIN SUPER MINIMOLD (UNIT: mm)



#### NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to the Vcc pin.
- (4) The DC cut capacitor must be attached to input pin and output pin.

#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).



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